L Number	Hits	Search Text	DB	Time stamp
4	2		USPAT	2003/10/16 09:44
5	65	("ONO") same (masking or protect\$5) same	USPAT;	2003/10/16 09:47
		((silicon adj nitride) or ("SiN")) same	US-PGPUB;	2000, 20, 20 05. 17
		(pattern\$6 or (wet adj etch\$6))	EPO; JPO;	
		(pacterny or (wee day etempo))	DERWENT;	ľ
		,	IBM TDB	
6	63	("ONO") same (masking or protect\$5) same	USPAT;	2003/10/16 09:47
6	63	((silicon adj nitride) or ("SiN")) same	US-PGPUB;	2003/10/10 09:47
		(pattern\$6 or (wet adj etch\$6)) and	EPO; JPO;	
1		(patternso of (wet adj etchso)) and   @ad<=20021115	DERWENT;	
		ead\-20021115	IBM TDB	
	12	(("6429063") or ("6417044") or ("6399441")	USPAT	2003/10/15 14:43
-	12	or ("6395590") or ("6372564") or	USFAI	2003/10/13 14:43
		("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or		
		("6518125") or ("6482708")).PN.		
	2		USPAT;	2003/09/02 14:33
-	2	((nitride adj read adj only adj memory) or		2003/03/02 14:33
		(nitride adj (read-only) adj memory)) and	US-PGPUB;	
		(ono same (wet adj etching) same (dop\$6 or	EPO; JPO;	
		implant\$6) same (buried adj bit adj line))	DERWENT;	
	_	/ /d: -b-b:\ (d66	IBM_TDB USPAT;	2003/09/02 14:12
-	2	<pre>(ono same (wet adj etching) same (dop\$6 or implant\$6) same (buried adj bit adj line))</pre>	USPAT; US-PGPUB;	2003/03/02 14:12
		and ((nitride adj read adj only adj	EPO; JPO;	
		memory) or (nitride adj (read-only) adj	DERWENT;	
	_	memory))	IBM_TDB USPAT;	2003/09/02 14:15
-	3	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and	US-PGPUB;	2003/03/02 14:15
		(nitride ad) (read-only) adj memory), and		
		ono and (wet adj etching) and (dop\$6 or implant\$6) and (buried adj bit adj line)	EPO; JPO; DERWENT;	
		implantso, and (buried ad) bit adj line)	IBM TDB	
	8	(/situide add wood add enly add mamary) or	USPAT;	2003/09/02 14:27
-	•	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and	US-PGPUB;	2003/09/02 14:27
1		ono and (wet adj etching) and (dop\$6 or	EPO; JPO;	·
		implant\$6) and (bit adj line)	DERWENT;	
		implantso, and (bit adj line)	IBM TDB	
_	94	((nitride adj read adj only adj memory) or	USPAT;	2003/09/02 14:33
	73	(nitride adj (read-only) adj memory)) and	US-PGPUB;	2003/03/02 14.33
		ono and (dop\$6 or implant\$6)	EPO; JPO;	
		One and (doppe of implanted)	DERWENT;	
			IBM TDB	
_	94	(((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:34
	, , ,	or (nitride adj (read-only) adj memory))	US-PGPUB;	
		and ono and (dop\$6 or implant\$6) ) and	EPO; JPO;	
		@ad<=20021115	DERWENT;	
			IBM TDB	
-	81	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:29
		or (nitride adj (read-only) adj memory))	US-PGPUB;	
		and ono and (dop\$6 or implant\$6) ) and	EPO; JPO;	
		@ad<=20021115) and bit	DERWENT;	
			IBM TDB	
] -	72	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:34
		or (nitride adj (read-only) adj memory))	US-PGPUB;	
		and ono and (dop\$6 or implant\$6) ) and	EPO; JPO;	
		@ad<=20021115) and (bit adj line)	DERWENT;	
			IBM_TDB	
-	2	((nitride adj read adj only adj memory) or	USPĀT;	2003/09/02 14:33
		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		nrom) and (ono same (wet adj etching) same	EPO; JPO;	
		(dop\$6 or implant\$6) same (buried adj bit	DERWENT;	
		adj line))	IBM_TDB	
-	157	((nitride adj read adj only adj memory) or	USPĀT;	2003/09/02 14:33
1		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	150		USPAT;	2003/09/02 14:34
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6) )	EPO; JPO;	
		and @ad<=20021115	DERWENT;	}
			IBM TDB	

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	read adj only adj memory) (read-only) adj memory) or	2003/09/0

				1 0000 100 100 1
-	115	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:46
İ		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6) ) and @ad<=20021115) and (bit adj line)	EPO; JPO; DERWENT;	
		and tadt-20021113) and (bit adj line)	IBM TDB	
1_	85	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
	03	or (nitride adj (read-only) adj memory) or	US-PGPUB;	2003/03/02 14:43
		NROM) and ono and (dop\$6 or implant\$6) )	EPO; JPO;	
		and @ad<=20021115) and (bit adj line)) and	DERWENT;	
		(etch\$5)	IBM TDB	
-	24	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:48
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6) )	EPO; JPO;	
		and @ad<=20021115) and (bit adj line)) and	DERWENT;	
		(wet adj etch\$5)	IBM_TDB	
-	30		USPAT;	2003/09/02 14:47
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and one and (dop\$6 or implant\$6) )	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj line)	DERWENT;	
1_	6	1 - 1	IBM_TDB USPAT;	2003/09/02 14:47
	ľ	memory) or (nitride adj (read-only) adj	US-PGPUB;	2003/09/02 14.47
		memory) or NROM) and one and (dop\$6 or	EPO; JPO;	
	Į.	implant\$6) ) and @ad<=20021115) and (bit	DERWENT;	
	ļ	adj line)) and (wet adj etch\$5)) and	IBM TDB	
		(bur\$4 adj bit adj line)	_	
-	6	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6) )	EPO; JPO;	
	1	and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
	2.0	line)) and (wet adj etch\$5)	IBM_TDB	2022/20/22 27 57
-	26	<pre>(((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or</pre>	USPAT; US-PGPUB;	2003/09/03 07:57
		NROM) and one and (dop\$6 or implant\$6) )	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
		line)) and (etch\$5)	IBM TDB	
-	99	((nitride adj read adj only adj memory) or	USPAT;	2003/09/03 10:52
		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		(NROM)) and ((ono or (oxide adj nitride	EPO; JPO;	
		adj oxide) or ((silicon adj oxide) adj	DERWENT;	
İ		(silicon adj nitride) adj (silicon adj	IBM_TDB	
		oxide))) and (dop\$6 or implant\$6) and		
		<pre>@ad&lt;=20021115) and (bit adj line) and (word adj line)</pre>		
_	1	("6566203").PN.	USPAT	2003/10/09 15:34
1 -	ī	("6461906").PN.	USPAT	2003/09/03 13:17
-	1	("5496753").PN.	USPAT	2003/09/03 13:07
-	329	(438/261).CCLS.	USPAT;	2003/09/03 13:07
			US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
	1 1 1 1 1 1 1 1 1	(430 (257) 6616	IBM_TDB	2002/00/02 12 22
-	1390	(438/257).CCLS.	USPAT;	2003/09/03 13:09
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
1-	578	(438/258).CCLS.	USPAT;	2003/09/03 13:08
]	]	·	US-PGPUB;	111, 15, 00 13.00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
[ -	330	(438/259).CCLS.	USPAT;	2003/09/03 13:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	98	(438/260).CCLS.	USPAT;	2003/09/03 13:08
	30	(130, 200, 10010.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM TDB	

[-	329	(438/261).CCLS.	USPAT;	2003/09/03 13:08
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	, ,
-	199	(438/262).CCLS.	USPAT;	2003/09/03 13:08
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	711	(438/526).CCLS.	IBM_TDB USPAT;	2003/09/03 13:09
-	/11	(436/326).CCLS.	US-PGPUB;	2003/03/03 13.09
			EPO; JPO;	
			DERWENT;	
1		·	IBM TDB	
l _	694	(438/275).CCLS.	USPAT;	2003/09/03 13:09
		(100, = 10, 100=01	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	246	(438/294).CCLS.	USPAT;	2003/09/03 13:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	152	(438/216).CCLS.	USPĀT;	2003/09/03 13:10
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	, _ , _ ,
-	333	(438/591).CCLS.	USPAT;	2003/09/03 13:10
		*	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	150	(429/216) CCIS	IBM_TDB	2003/00/03 13:10
-	152	(438/216).CCLS.	USPAT; US-PGPUB;	2003/09/03 13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	613	(438/264).CCLS.	USPAT;	2003/09/03 13:11
		•	US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	636	(438/527).CCLS.	USPAT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/00 10 10
_	750	(438/287).CCLS.	USPĀT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	74	(438/954) CCI S	USPAT;	2003/09/03 13:12
-	'4	(438/954).CCLS.	US-PGPUB;	2003/03/03 13:12
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	20	semiconductor same ono same (etch\$4 adj	USPAT;	2003/09/03 15:28
		stop)	US-PGPUB;	= = = = = = = = = = = = = = = = = = =
	]		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	20	(semiconductor same ono same (etch\$4 adj	USPAT;	2003/09/03 15:27
		stop)) and @ad<=20021115	US-PGPUB;	
	1		EPO; JPO;	
	]		DERWENT;	
			IBM_TDB	

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[-	480	semiconductor and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB;	2003/09/15 14:21
			EPO; JPO; DERWENT;	
-	12	438/287,261,591.ccls. and ono and (etch	IBM_TDB USPAT; US-PGPUB;	2003/09/15 14:37
-		adj stop) and @ad<=20021115	EPO; JPO; DERWENT;	
	264	429/297 261 501 gala and one and	IBM_TDB USPAT;	2003/09/03 15:38
_	264	438/287,261,591.ccls. and ono and @ad<=20021115	US-PGPUB; EPO; JPO;	2003/03/03 13:38
			DERWENT; IBM TDB	
_	397	257/\$.ccls. and ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<=20021115	USPĀT; US-PGPUB;	2003/09/15 14:52
			EPO; JPO; DERWENT;	
_	340		IBM_TDB USPAT;	2003/09/15 14:52
		adj (layer or film)) and @ad<=20021115	US-PGPUB; EPO; JPO;	
	500	and (analysis of and (laves an	DERWENT; IBM_TDB USPAT;	2003/09/15 14:53
-	502	ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<=20021115	US-PGPUB; EPO; JPO;	2003/09/13 14:33
			DERWENT; IBM TDB	
-	9	(ono same semiconductor same (etch\$3 adj stop\$4 adj (layer or film))) and	USPĀT; US-PGPUB;	2003/09/15 14:53
<u>}</u>		@ad<=20021115	EPO; JPO; DERWENT;	
-	478	ono and semiconductor and (etch\$3 adj	IBM_TDB USPAT;	2003/09/15 15:34
		stop\$4 adj (layer or film)) and @ad<=20021115	US-PGPUB; EPO; JPO; DERWENT;	
_	32968	liu.in.	IBM_TDB USPAT;	2003/09/15 15:36
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
_	10	liu.in. and cheng-jye	USPĀT; US-PGPUB;	2003/09/15 15:35
			EPO; JPO; DERWENT; IBM TDB	
_	2054	hsiung.in.	USPAT; US-PGPUB;	2003/09/15 15:36
			EPO; JPO; DERWENT;	
_	66294	chen.in.	IBM_TDB USPAT;	2003/09/15 15:36
			US-PGPUB; EPO; JPO; DERWENT;	
_	3	hsiung.in. and tai-liang	IBM_TDB USPAT;	2003/09/15 15:37
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
-	32	chen.in. and chia-hsing	USPAT; US-PGPUB;	2003/09/15 15:37
			EPO; JPO; DERWENT; IBM TDB	
-	1	("6376341").PN.	USPAT	2003/10/10 11:29

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-	3	(("6566203") or ("6461906") or	USPAT	2003/10/10 10:48
		("5496753")).PN.		
-	13	(("6429063") or ("6417044") or ("6399441")	USPAT	2003/10/15 14:49
		or ("6395590") or ("6372564") or		İ
		("6346466") or ("6255166") or ("6583007")		
		or ("6566203") or ("6555427") or		
		("6518125") or ("6482708") or		
		("6376341")).PN.		
-	14	(("6429063") or ("6417044") or ("6399441")	USPAT	2003/10/16 09:22
		or ("6395590") or ("6372564") or		
		("6346466") or ("6255166") or ("6583007")		
		or ("6566203") or ("6555427") or		1
		("6518125") or ("6482708") or ("6376341")		
		or ("6538270")).PN.		

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